

FIG. 1

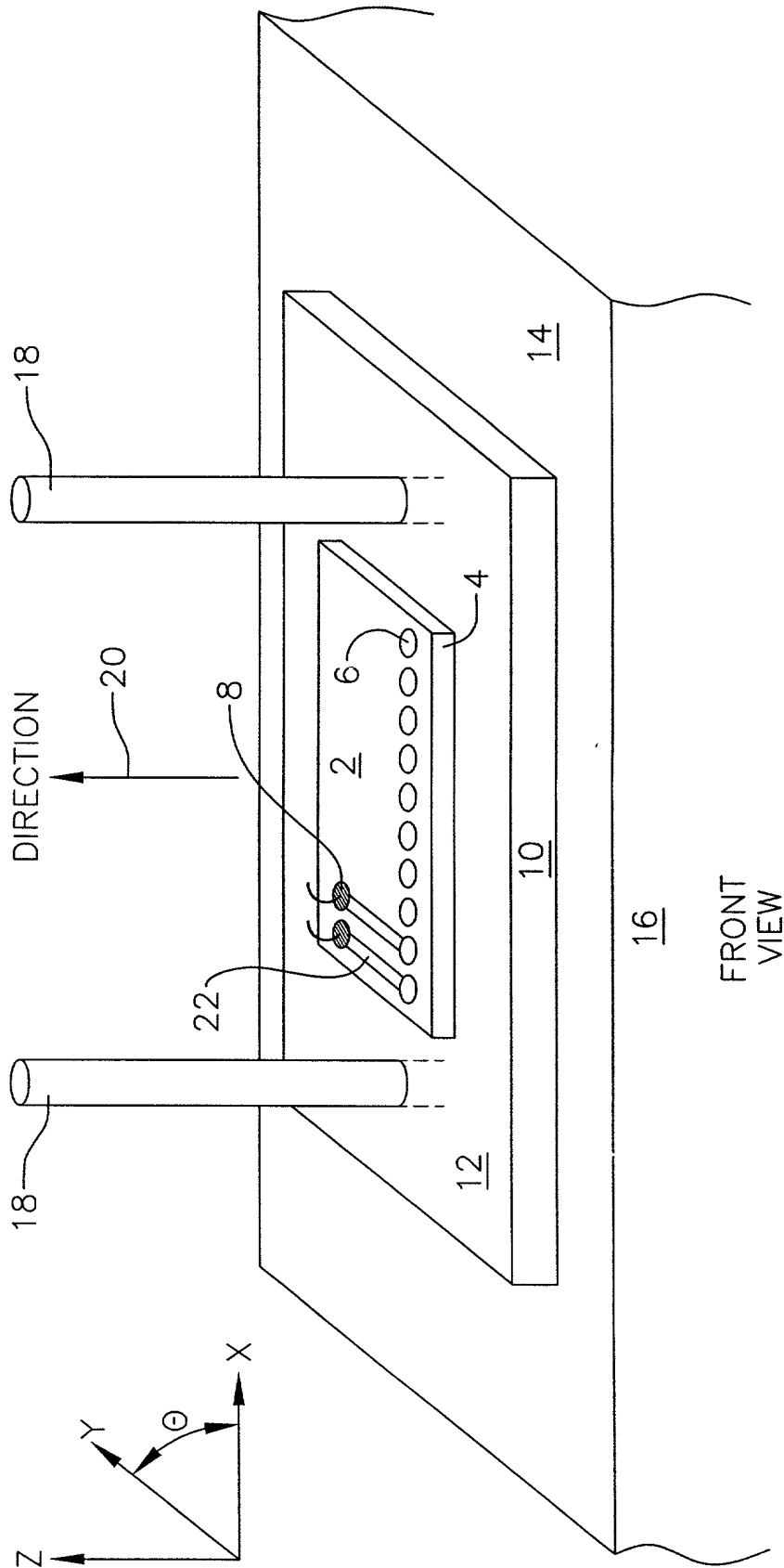


FIG. 2

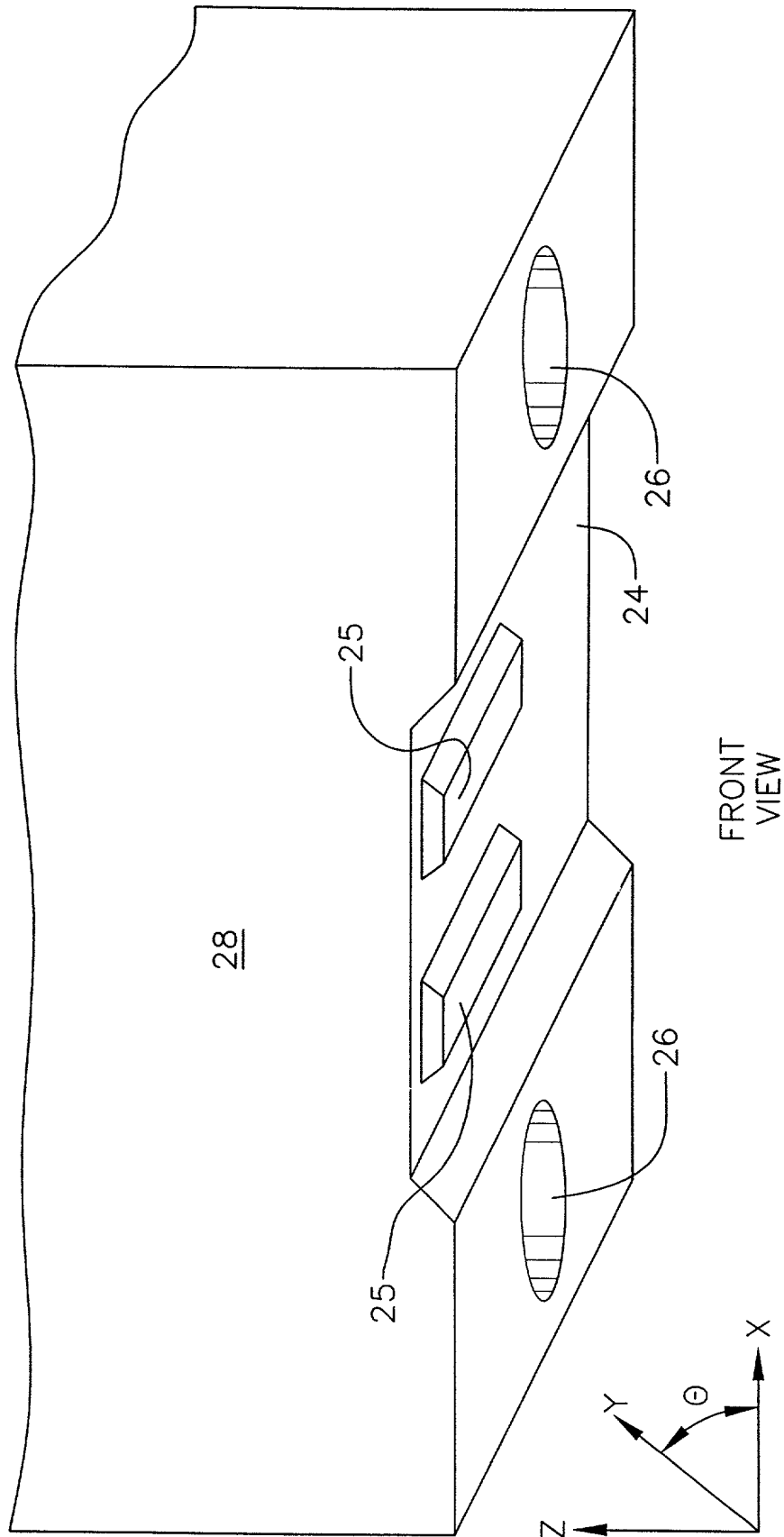


FIG. 3A

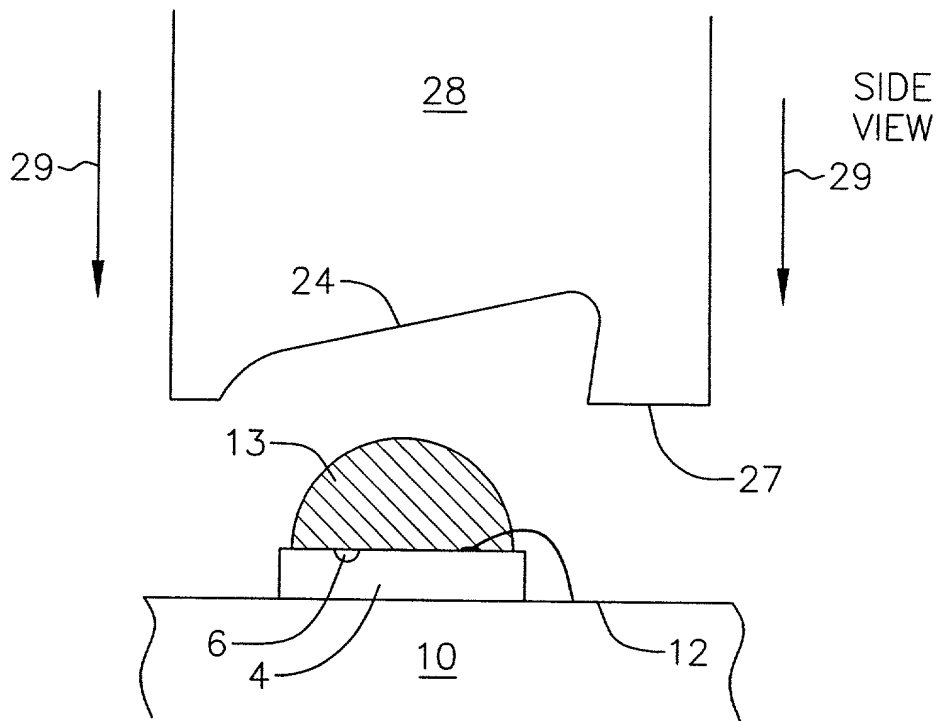


FIG. 3B

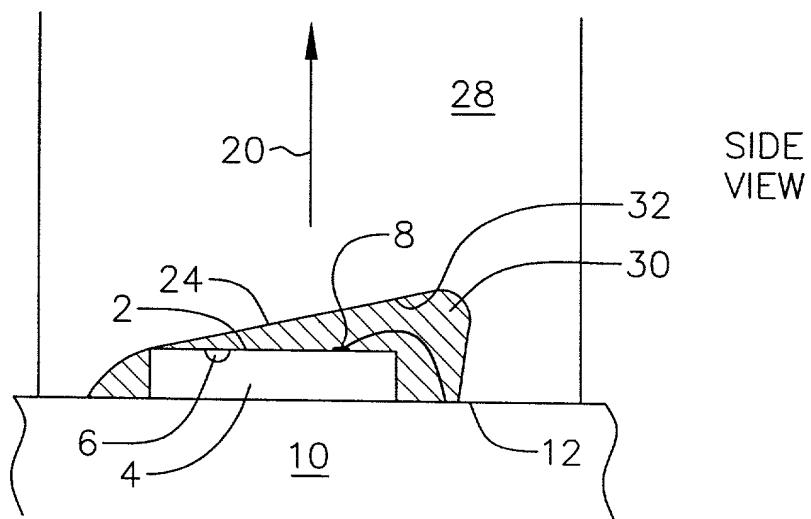
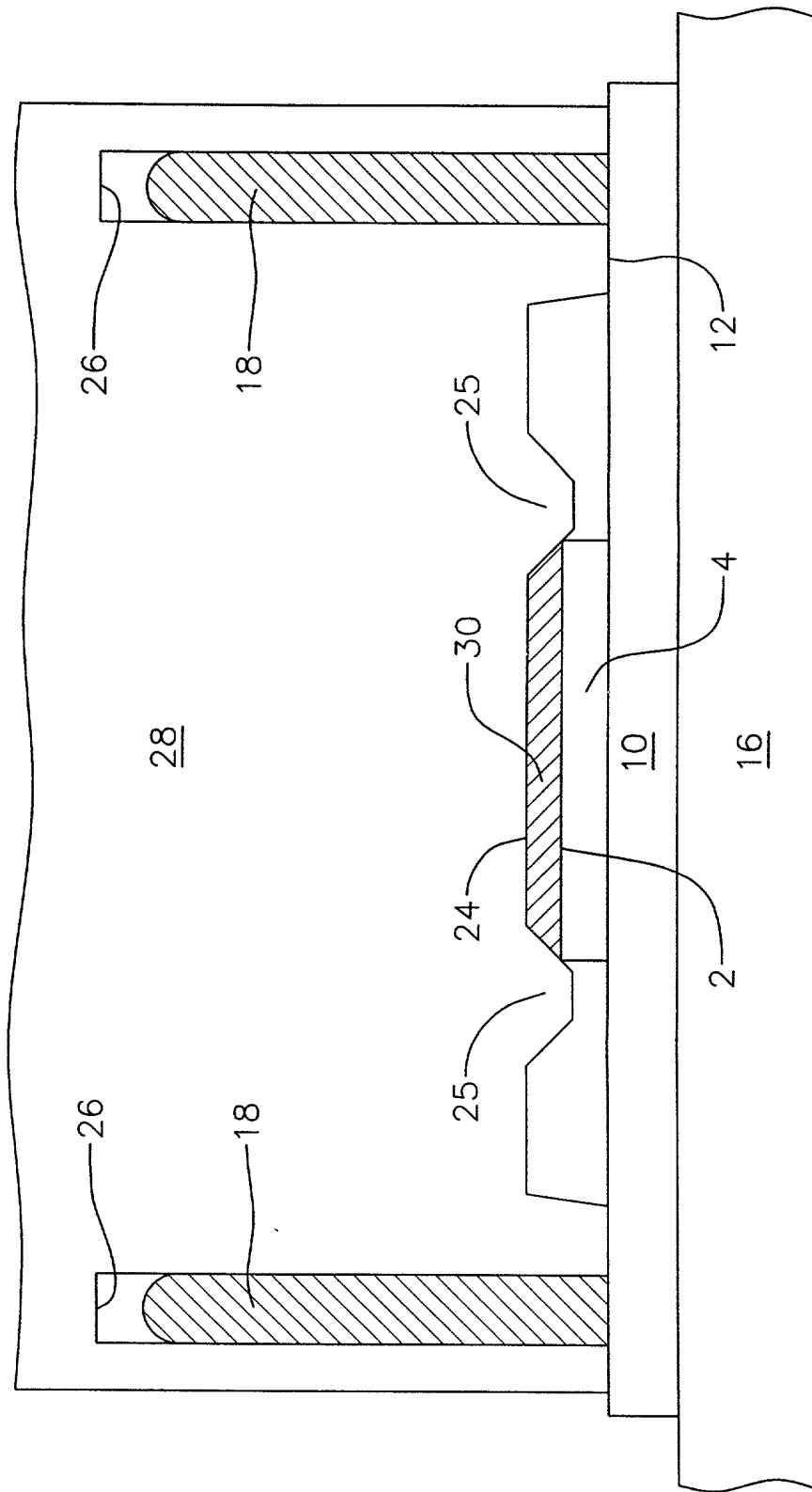
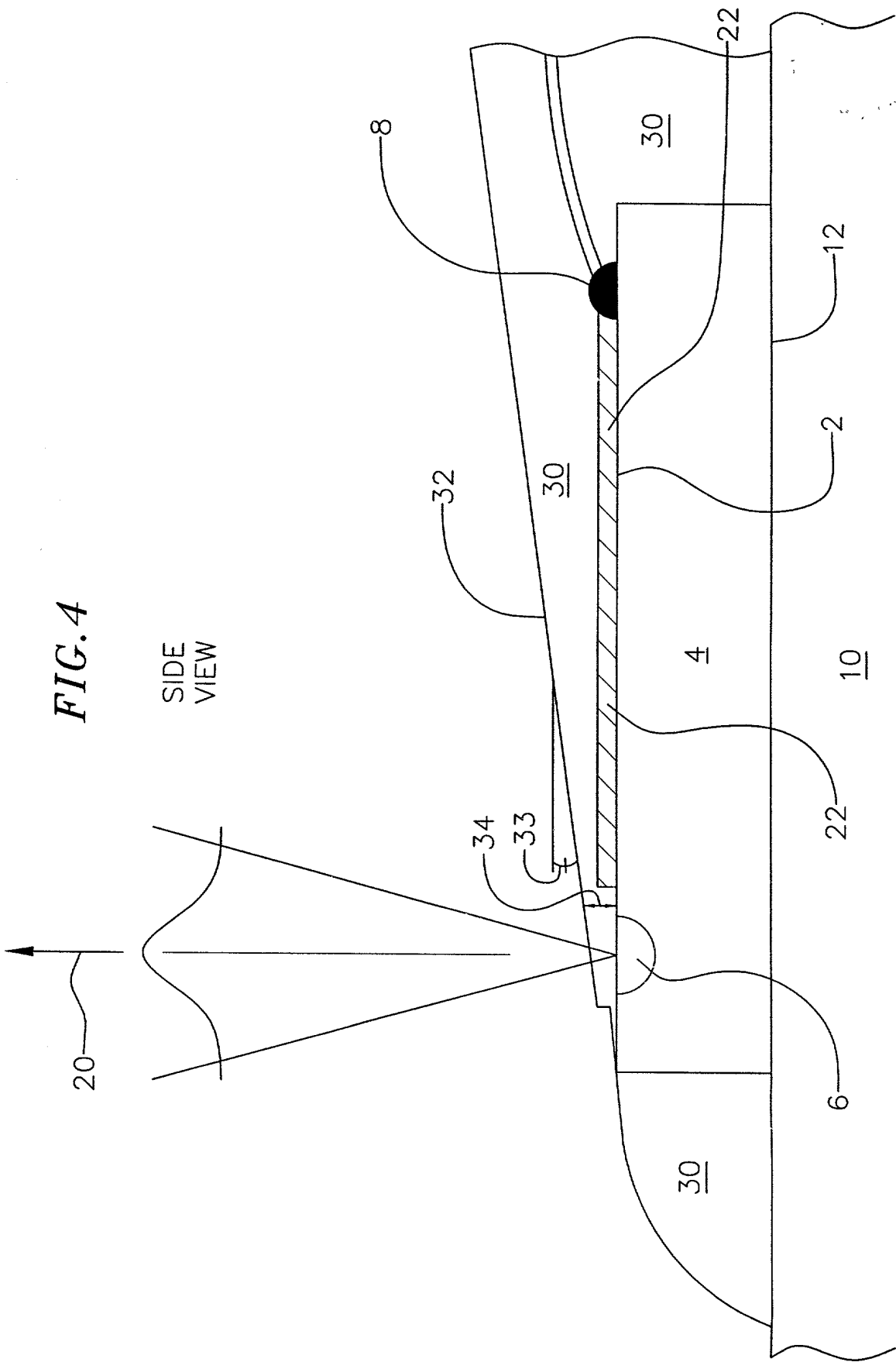


FIG. 3C

FRONT
VIEW





This cross-sectional view shows a substrate 12 with a layer 10 on its surface. A rectangular block 6 is positioned on layer 10. A dome-shaped structure 13, filled with diagonal hatching, sits on top of block 6. A small circular feature 4 is located at the base of the dome 13 where it meets block 6. Above the dome, a complex structure 24 is formed, featuring a sloped surface 29 and a vertical section 27. Two downward-pointing arrows, both labeled 29, indicate a force or pressure being applied to the top surface of structure 24.

This diagram shows a cross-section of a semiconductor device. It features a substrate 10 with a gate stack 6 on top. A channel layer 8 is formed over the gate stack. A drain region 24 is located to the left of the channel layer. A vertical arrow 20 points upwards from the center of the channel layer. Other labels include 2, 4, 6, 8, 10, 12, 20, 24, 28, 29, and 30.

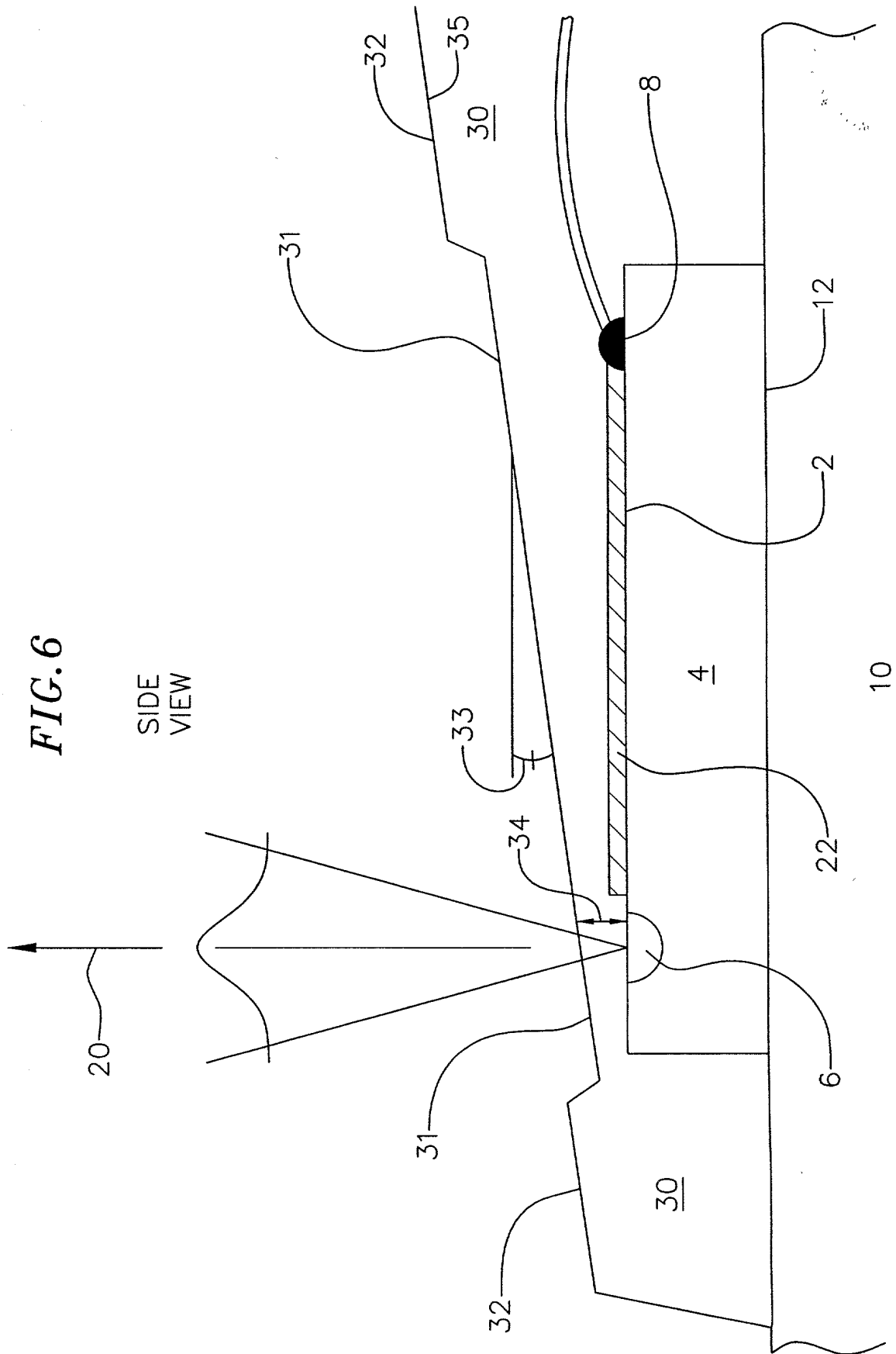


FIG. 7

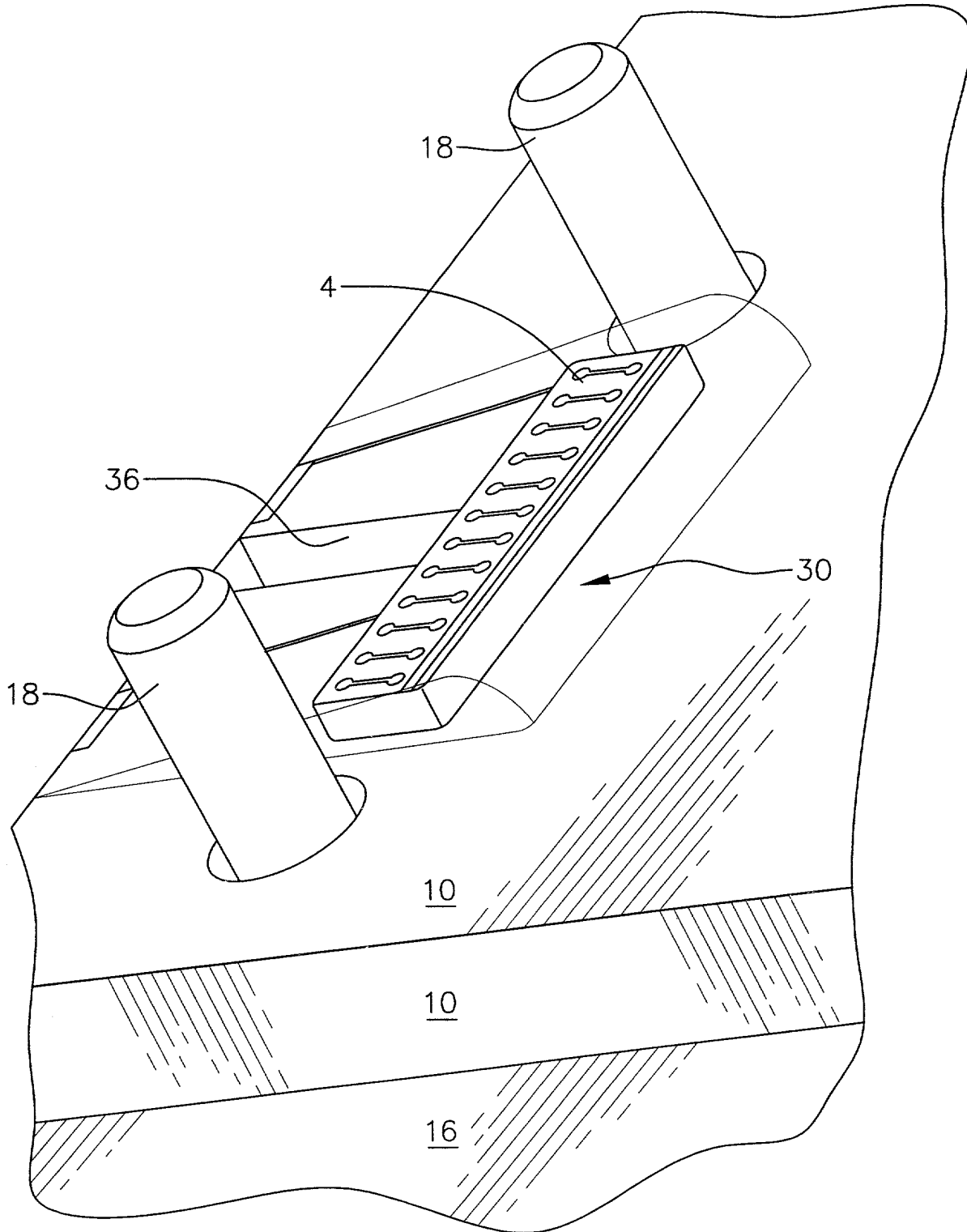


FIG. 8

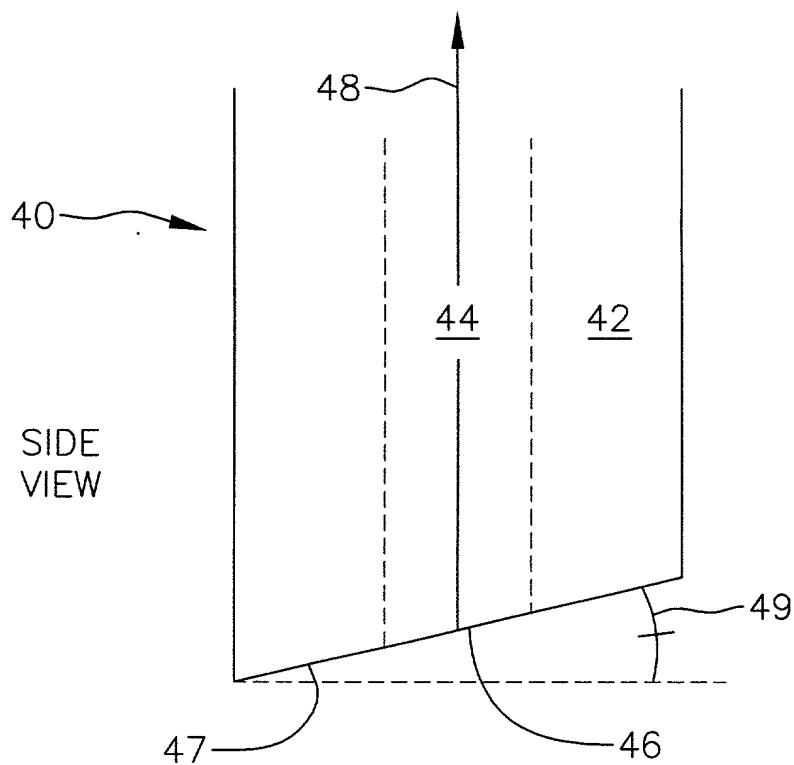


FIG. 9

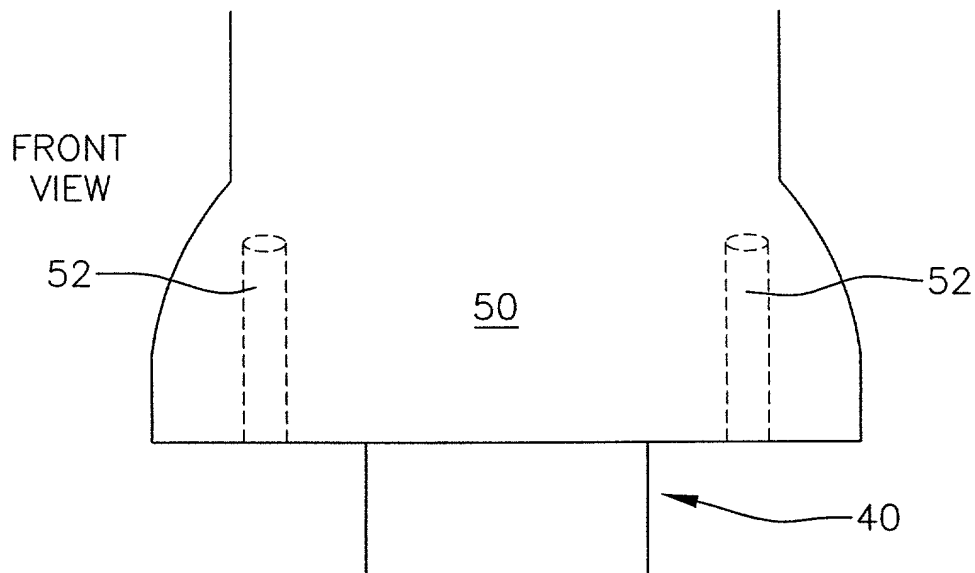


FIG. 10

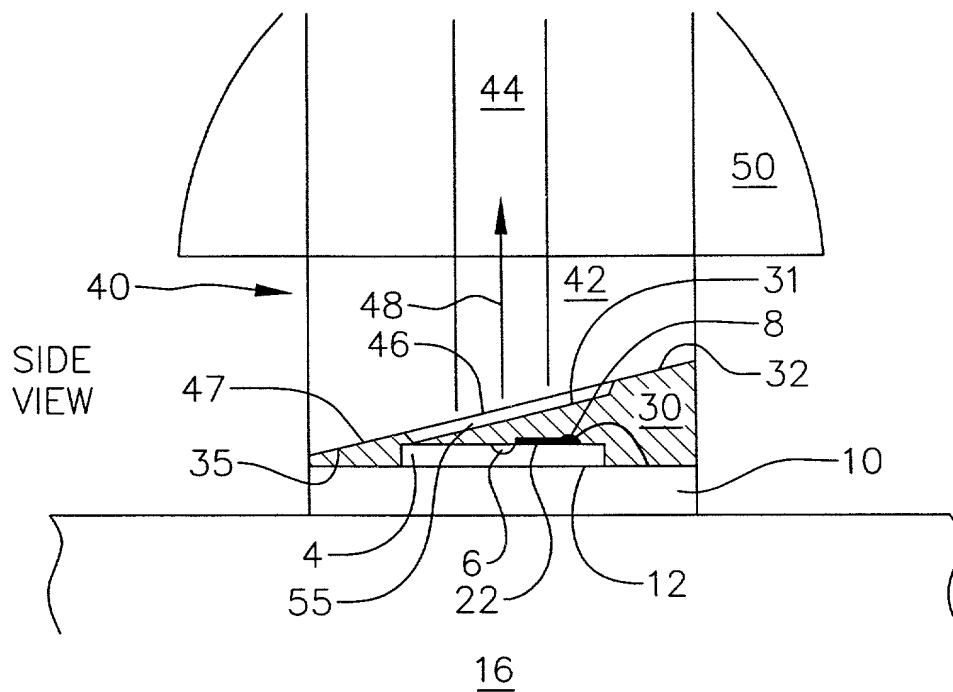


FIG. 11

